AH116

1/2 Watt, High Linearity InGaP HBT Amplifier

The Communications Edge ™

Product Information

Product Features

- 800 – 1000 MHz
- +28 dBm P1dB
- +42 dBm Output IP3
- 17 dB Gain @ 900 MHz
- Single Positive Supply (+5 V)
- MTTF >100 Years
- SOIC-8 SMT Package

Applications

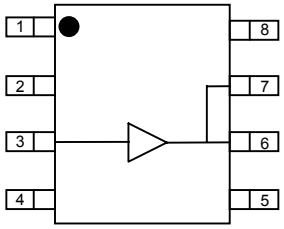
- Mobile Infrastructure
- Final Stage Amplifier for Repeaters

Product Description

The AH116 is a high dynamic range driver amplifier in a low-cost surface mount package. The InGaP/GaAs HBT is able to achieve high performance for various narrow-band tuned application circuits with up to +42 dBm OIP3 and +28 dBm of compressed 1-dB power and is housed in an industry standard SOIC-8 SMT package. All devices are 100% RF and DC tested.

The product is targeted for use as driver amplifiers for wireless infrastructure where high linearity and medium power is required. The internal active bias allows the AH116 to maintain high linearity over temperature and operate directly off a +5 V supply. This combination makes the device an excellent fit for transceiver line cards and power amplifiers in current and next generation multi-carrier 3G base stations.

Functional Diagram



Function	Pin No.
Vref	1
Input / Base	3
Output / Collector	6, 7
Vbias	8
GND	Backside
N/C or GND	2, 4, 5

Specifications

Parameters	Units	Min	Typ	Max
Frequency Range	MHz	800	900	1000
S21 - Gain	dB	15	17	
S11 - Input R.L.	dB		-18	
S22 - Output R.L.	dB		-7	
Output P1dB	dBm	+27	+28	
Output IP3 (2)	dBm	+42	+42	
IS-95A Channel Power @ -45 dBc ACPR, 900 MHz	dBm		+23	
Noise Figure	dB		7	
Operating Current Range (3)	mA	200	250	300
Device Voltage	V		+5	

Test conditions unless otherwise noted.
1. T = 25ºC, Vsupply = +5 V, Frequency = 900 MHz, in tuned application circuit.
2. 3OIP measured with two tones at an output power of +13 dBm/tone separated by 1 MHz. The suppression on the largest IM3 product is used to calculate the 3OIP using a 2:1 rule.
3. This corresponds to the quiescent current or operating current under small-signal conditions. It is expected that the current can increase up to 300mA at P1dB.

Absolute Maximum Rating

Parameters	Rating
Operating Case Temperature	-40 to +85 °C
Storage Temperature	-65 to +150 °C
RF Input Power (continuous)	+20 dBm
Device Voltage	+8 V
Device Current	400 mA
Device Power	2 W

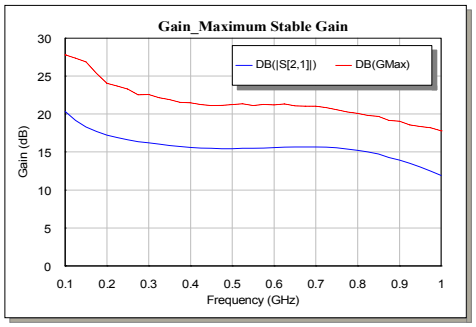
Operation of this device above any of these parameters may cause permanent damage.

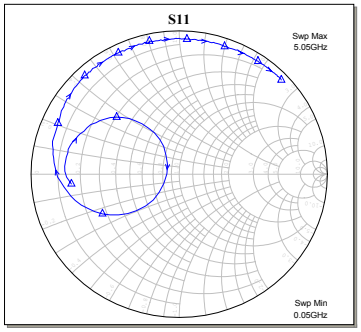
Ordering Information

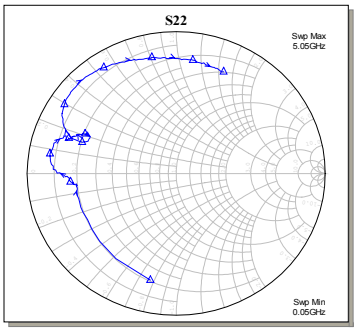
Part No.	Description
AH116-S8	1/2 Watt, High Linearity InGaP HBT Amplifier
AH116-S8PCB900	900 MHz Evaluation Board

Typical Device Data

S-Parameters (V_{cc} = +5 V, I_{cc} = 250 mA, T = 25°C, unmatched 50 ohm system)





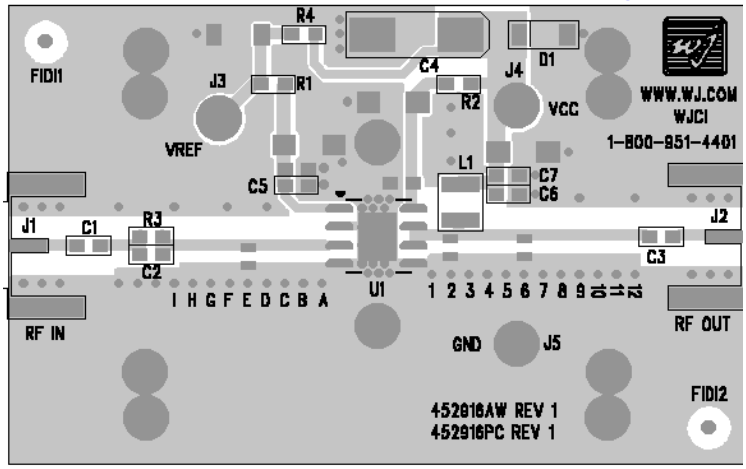


Notes:
The gain for the unmatched device in 50 ohm system is shown as the trace in black color. For a tuned circuit for a particular frequency, it is expected that actual gain will be higher, up to the maximum stable gain. The maximum stable gain is shown in the dashed red line. The return loss plots are shown from 50 – 5050 MHz, with markers placed at 0.5 – 5.05 GHz in 0.5 GHz increments.

S-Parameters (V_{cc} = +5 V, I_{cc} = 250 mA, T = 25°C, unmatched 50 ohm system, calibrated to device leads)

Freq (MHz)	S11 (dB)	S21 (dB)	S21 (ang)	S12 (dB)	S12 (ang)	S22 (dB)	S22 (ang)
50	-2.72	24.16	133.35	-36.72	29.75	-2.23	-102.97
100	-2.25	20.33	124.95	-35.31	13.96	-3.08	-137.03
200	-2.31	17.23	119.37	-34.90	2.32	-3.32	-159.63
400	-3.08	15.63	98.28	-33.62	-16.36	-3.48	-172.70
600	-5.79	15.58	69.70	-32.10	-37.73	-2.87	-176.25
800	-19.72	15.22	25.60	-31.19	-78.95	-2.27	-179.74
1000	-6.06	11.91	-22.67	-33.26	-129.67	-1.40	173.15
1200	-2.34	6.92	-56.59	-38.16	176.95	-1.49	165.12
1400	-1.28	2.28	-78.59	-41.14	132.98	-1.96	160.84
1600	-0.91	-1.17	-96.56	-42.62	113.65	-2.53	160.80
1800	-0.71	-4.40	-112.20	-40.78	98.57	-2.92	157.57
2000	-0.60	-6.78	-128.36	-40.27	74.44	-3.29	155.77
2200	-0.58	-8.70	-146.80	-37.79	53.03	-3.72	155.24
2400	-0.55	-9.87	-169.80	-39.90	53.88	-3.96	158.19
2600	-0.51	-10.59	160.74	-37.66	41.18	-3.25	160.80
2800	-0.51	-11.66	128.82	-35.78	31.88	-1.97	158.05
3000	-0.54	-13.08	95.01	-35.88	27.61	-1.09	149.64

Application Circuit PC Board Layout

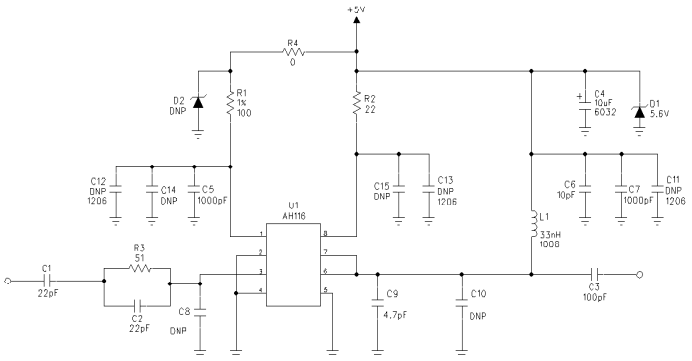


Circuit Board Material: .014" Getek, 4 - layer, 1 oz copper, Microstrip line details: width = .026", spacing = .026"
The silk screen markers 'A', 'B', 'C', etc. and '1', '2', '3', etc. are used as placemarkers for the input and output tuning Shunt capacitors – C8 and C9. The markers and vias are spaced in .050" increments.

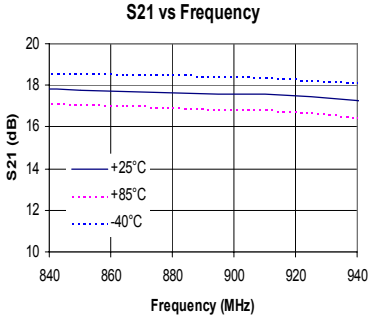
900 MHz Application Circuit (AH116-S8PCB900)

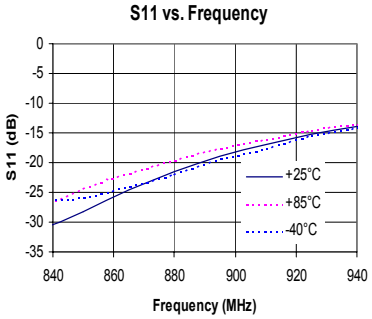
Typical RF Performance at 25°C

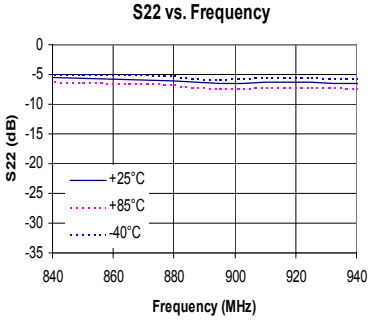
Frequency	900 MHz
S21 – Gain	17 dB
S11 – Input Return Loss	-18 dB
S22 – Output Return Loss	-7 dB
Output P1dB	+28 dBm
Output IP3 (+17 dBm / tone, 1 MHz spacing)	+42 dBm
Channel Power ((@-45 dBc ACPR, IS-95 9 channels fwd)	+23 dBm
Noise Figure	7 dB
Device / Supply Voltage	+5 V
Quiescent Current	250 mA

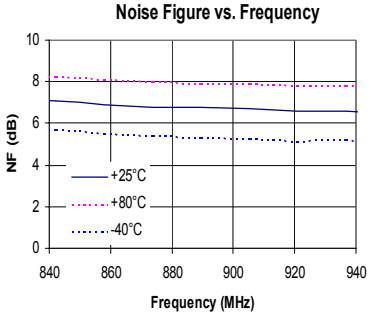


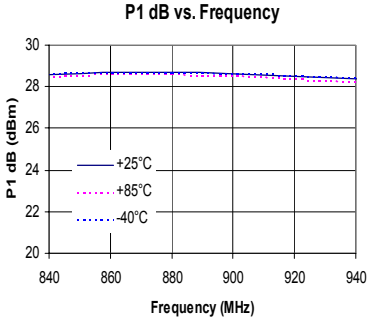
C9 is placed at the silkscreen marker '11' or center of component placed at 29 deg. @ 960 MHz away from pin 6. DNP represents "Do not populate".

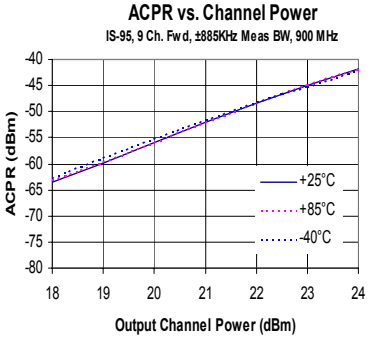


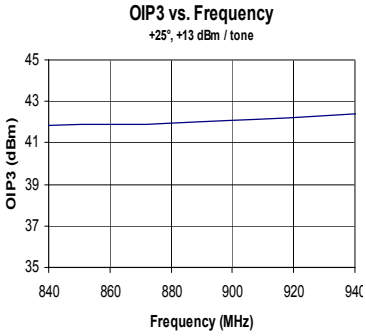


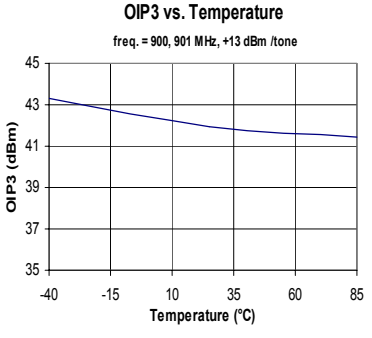


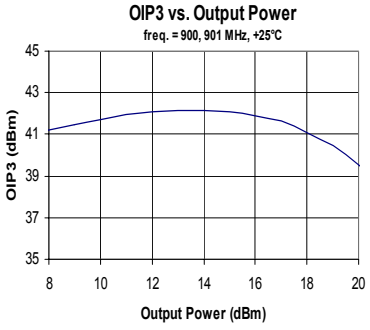












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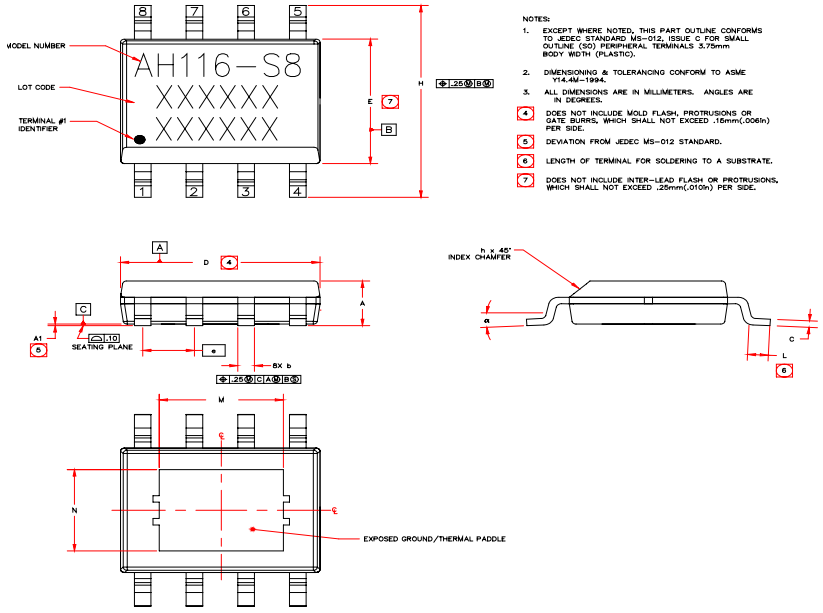
Product Information

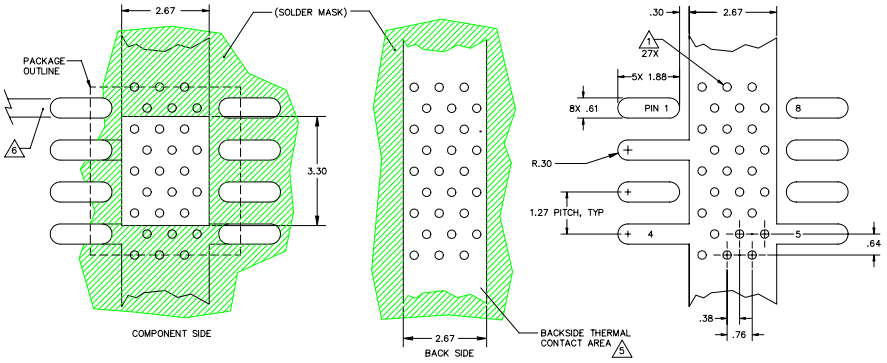
Outline Drawing



NOTES:
1. EXCEPT WHERE NOTED, THIS PART OUTLINE CONFORMS TO JEDEC STANDARD MS-012, ISSUE C FOR SMALL OUTLINE (SO) PERIPHERAL TERMINALS 3.75mm BODY WIDTH (PLASTIC).
2. DIMENSIONING & TOLERANCING CONFORM TO ASME Y14.4M-1994.
3. ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES.
4. DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS, WHICH SHALL NOT EXCEED .16mm(.006in) PER SIDE.
5. DEVIATION FROM JEDEC MS-012 STANDARD.
6. LENGTH OF TERMINAL FOR SOLDERING TO A SUBSTRATE.
7. DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSIONS, WHICH SHALL NOT EXCEED .25mm(.010in) PER SIDE.

SYMBOL	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	1.30	1.50	.051	.059
A1	0	.10	0	.004
b	.38	.43	.015	.017
C	.18	.23	.007	.009
D	4.80	5.00	.189	.197
E	3.80	4.00	.150	.157
e	1.27 BSC		.050 BSC	
H	5.80	6.20	.228	.244
h	.25	.50	.01	.02
L	.40	1.27	.016	.050
M	2.95	3.15	.116	.124
N	2.03	2.54	.080	.100
α	0	8°	0	8°

Land Pattern

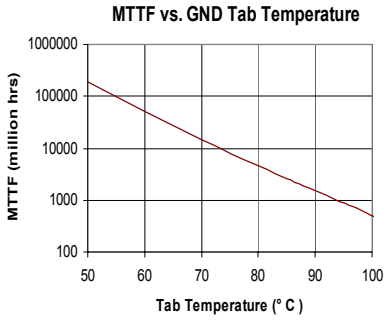


Thermal Specifications

Parameter	Rating
Operating Case Temperature	-40 to +85° C
Thermal Resistance[1], Rth	62° C / W
Junction Temperature[2], Tjc	162 °C

Notes:

1. The thermal resistance is referenced from the junction-to-case at a case temperature of 85° C. Tjc is a function of the voltage at pins 6 and 7 and the current applied to pins 6, 7, and 8 and can be calculated by:
   Tjc = Tcase + Rth * Vd * Id
2. This corresponds to the typical biasing condition of +5V, 250 mA at an 85° C case temperature. A minimum MTTF of 1 million hours is achieved for junction temperatures below 247° C.



Product Marking

The component will be marked with an "AH116-S8" designator with an alphanumeric lot code on the top surface of the package. Tape and reel specifications for this part is located on the website in the "Application Notes" section.

ESD / MSL Information

ESD Rating:	Class 1B
Value:	Passes at between 500 and 1000V
Test:	Human Body Model (HBM)
Standard:	JEDEC Standard JESD22-A114
MSL Rating:	Level 3 at +240 °C convection reflow
Standard:	JEDEC Standard J-STD-020A

Caution! ESD sensitive device.

Mounting Config. Notes

1. Ground / thermal vias are critical for the proper performance of this device. Vias should use a .35mm (#80 / .0135") diameter drill and have a final plated thru diameter of .25 mm (.010").
2. Add as much copper as possible to inner and outer layers near the part to ensure optimal thermal performance.
3. Mounting screws can be added near the part to fasten the board to a heatsink. Ensure that the ground / thermal via region contacts the heatsink.
4. Do not put solder mask on the backside of the PC board in the region where the board contacts the heatsink.
5. RF trace width depends upon the PC board material and construction.
6. Use 1 oz. Copper minimum.
7. All dimensions are in millimeters (inches). Angles are in degrees.